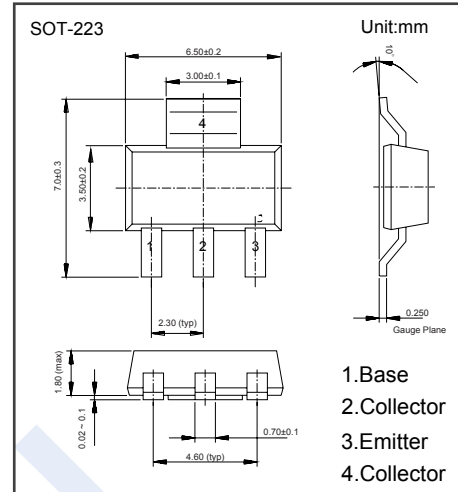


PNP Transistors

PZTA92 (KZTA92)

■ Features

- High Voltage Driver Applications
- Complementary to PZTA42

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-300	V
Collector - Emitter Voltage	V_{CE0}	-300	
Emitter - Base Voltage	V_{EB0}	-5	
Collector Current - Continuous	I_C	-200	mA
Collector Current - Pulse	I_{CP}	-500	
Collector Power Dissipation	P_C	1	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	125	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = -100 \mu\text{A}, I_E = 0$	-300			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = -1 \text{ mA}, I_B = 0$	-300			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -100 \mu\text{A}, I_C = 0$	-5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -200 \text{ V}, I_E = 0$			-250	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4 \text{ V}, I_C = 0$			-100	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -20 \text{ mA}, I_B = -2 \text{ mA}$			-0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -20 \text{ mA}, I_B = -2 \text{ mA}$			-0.9	
DC current gain	$h_{FE(1)}$	$V_{CE} = -10 \text{ V}, I_C = -1 \text{ mA}$	25			
	$h_{FE(2)}$	$V_{CE} = -10 \text{ V}, I_C = -10 \text{ mA}$	40			
	$h_{FE(3)}$	$V_{CE} = -10 \text{ V}, I_C = -30 \text{ mA}$	25			
Collector output capacitance	C_{ob}	$V_{CB} = -20 \text{ V}, I_E = 0, f = 1 \text{ MHz}$			6	pF
Transition frequency	f_T	$V_{CE} = -20 \text{ V}, I_C = -10 \text{ mA}, f = 100 \text{ MHz}$	50			MHz

PNP Transistors

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Typical Characteristics

